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1	2861539	@ad<19990615	USPAT	2004/09/06 16:58
2	30005	recombinat\$	USPAT	2004/09/06 16:58
3	58551	tunnel\$	USPAT	2004/09/06 16:58
4	1686	recombinat\$ and tunnel\$	USPAT	2004/09/06 16:58
5	168	recombinat\$ with tunnel\$	USPAT	2004/09/06 16:59
6	124	@ad<19990615 and (recombinat\$ with tunnel\$)	USPAT	2004/09/06 16:59
7	35865	Poole\$	USPAT	2004/09/06 16:59
8	0	(@ad<19990615 and (recombinat\$ with tunnel\$)) and Poole\$	USPAT	2004/09/06 16:59
9	88	Poole\$ same barrier	USPAT	2004/09/06 17:00
10	102	poole-frenkel	USPAT	2004/09/06 17:00
11	14	poole-frenkel same barrier	USPAT	2004/09/06 17:00
12	7	@ad<19990615 and (poole-frenkel same barrier)	USPAT	2004/09/06 17:12
13	0	dirac with coulomb\$ with tunnel\$	USPAT	2004/09/06 17:16
14	2	dirac same coulomb\$ sametunnel\$	USPAT	2004/09/06 17:15
16	2	dirac same coulomb\$	USPAT	2004/09/06 17:15
17	2	@ad<19990615 and (dirac same coulomb\$)	USPAT	2004/09/06 17:15
18	6	dirac with tunnel\$	USPAT	2004/09/06 17:16
19	15	dirac same tunnel\$	USPAT	2004/09/06 17:16
20	13	@ad<19990615 and (dirac same tunnel\$)	USPAT	2004/09/06 17:28
21	453	703/6.ccls.	USPAT	2004/09/06 17:28
22	505	703/13.ccls.	USPAT	2004/09/06 17:28
23	489	703/14.ccls.	USPAT	2004/09/06 17:28
24	113	257/366.ccls.	USPAT	2004/09/06 17:34
25	428	438/158.ccls.	USPAT	2004/09/06 17:34
26	199	438/172.ccls.	USPAT	2004/09/06 17:34
27	2066	703/6.ccls. or 703/13.ccls. or 703/14.ccls. or 257/366.ccls. or 438/158.ccls. or 438/172.ccls.	USPAT	2004/09/06 17:34
28	1606	@ad<19990615 and (703/6.ccls. or 703/13.ccls. or 703/14.ccls. or 257/366.ccls. or 438/158.ccls. or 438/172.ccls.)	USPAT	2004/09/06 17:35
29	14	(@ad<19990615 and (703/6.ccls. or 703/13.ccls. or 703/14.ccls. or 257/366.ccls. or 438/158.ccls. or 438/172.ccls.)) and dirac	USPAT	2004/09/06 17:35
30	79	(@ad<19990615 and (703/6.ccls. or 703/13.ccls. or 703/14.ccls. or 257/366.ccls. or 438/158.ccls. or 438/172.ccls.)) and tunnel\$	USPAT	2004/09/06 17:35
31	10	(@ad<19990615 and (703/6.ccls. or 703/13.ccls. or 703/14.ccls. or 257/366.ccls. or 438/158.ccls. or 438/172.ccls.)) and coulomb\$	USPAT	2004/09/06 17:36

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1 Capacitances in double-barrier tunneling structures

Genoe, J.; Van Hoof, C.; Van Roy, W.; Smet, J.H.; Fobelets, K.; Mertens, R.P. Borghs, G.;

 Electron Devices, IEEE Transactions on , Volume: 38 , Issue: 9 , Sept. 1991
 Pages:2006 - 2012

[\[Abstract\]](#) [\[PDF Full-Text \(548 KB\)\]](#) **IEEE JNL**

2 Temperature model for current gain of tunnelling field-induced junction transistors

Zhen Jiang; Wei Tongli; Feng Yaolan;

 Electronics Letters , Volume: 25 , Issue: 6 , 6 March 1989
 Pages:419 - 420

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3 Fast interface characterization of tunnel oxide MOS structures

Sell, B.; Schumann, D.; Krautschneider, W.H.;

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4 Voltage- and temperature-dependent gate capacitance and current model: application to ZrO/sub 2/ n-channel MOS capacitor

Yang-Yu Fan; Nieh, R.E.; Lee, J.C.; Lucovsky, G.; Brown, G.A.; Register, L.F. Banerjee, S.K.;

 Electron Devices, IEEE Transactions on , Volume: 49 , Issue: 11 , Nov. 2002
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[\[Abstract\]](#) [\[PDF Full-Text \(509 KB\)\]](#) IEEE JNL

5 **Numerical simulation of the current-voltage characteristics of heteroepitaxial Schottky-barrier diodes**

Bhapkar, U.V.; Mattauch, R.J.;

Electron Devices, IEEE Transactions on , Volume: 40 , Issue: 6 , June 1993
Pages:1038 - 1046

[\[Abstract\]](#) [\[PDF Full-Text \(684 KB\)\]](#) IEEE JNL

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